

RJK4518DPK

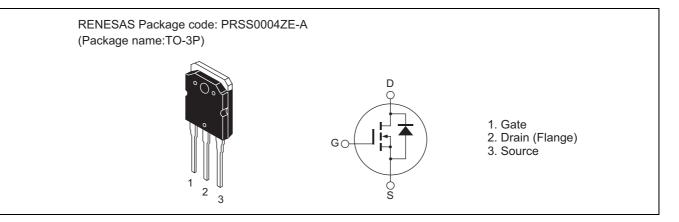
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1529-0100 Rev.1.00 Mar 20, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	450	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	39	А
Drain peak current	I _{D (pulse)} Note1	117	А
Body-drain diode reverse drain current	I _{DR}	39	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	117	А
Avalanche current	I _{AP} ^{Note3}	10	А
Avalanche energy	E _{AR} ^{Note3}	5.6	mJ
Channel dissipation	Pch ^{Note2}	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C



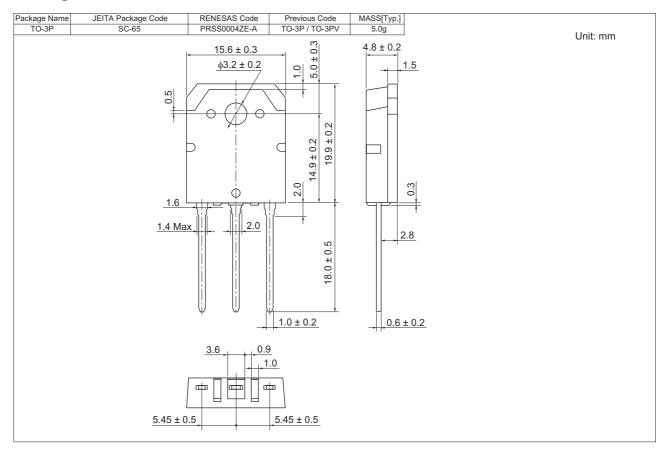
Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	450	—		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 450 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.11	0.13	Ω	$I_D = 19.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	4100		pF	V _{DS} = 25 V
Output capacitance	Coss	_	440		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	45		pF	
Turn-on delay time	t _{d(on)}	_	51		ns	I _D = 19.5 A
Rise time	tr	_	118		ns	$V_{GS} = 10 V$ $R_L = 11.5 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	128		ns	
Fall time	t _f	_	91		ns	
Total gate charge	Qg	—	93		nC	V _{DD} = 360 V
Gate to source charge	Qgs	_	21		nC	V _{GS} = 10 V I _D = 39 A
Gate to drain charge	Qgd	_	40		nC	
Body-drain diode forward voltage	V _{DF}	_	0.96	1.60	V	$I_F = 39 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		390	—	ns	$I_F = 39 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK4518DPK-00-T0	360 pcs	Box (Tube)



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